



Description

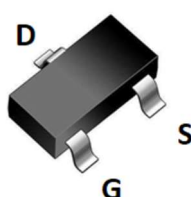
JMT P-channel Enhancement Mode Power MOSFET

Features

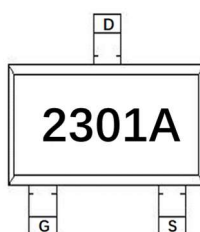
- $V_{DS} = -20V$, $I_D = -3A$
 $R_{DS(ON)} < 64m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 89m\Omega$ @ $V_{GS} = -2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

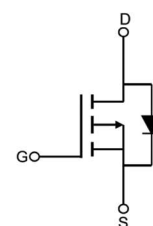
- PWM Applications
- Load Switch
- Power Management



SOT-23 top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
2301A	JMTL2301A	TAPING	SOT-23	7inch	3000	180000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	A
		$T_A = 100^\circ C$	
I_{DM}	Pulsed Drain Current ^{note1}	-12	A
P_D	Power Dissipation	0.9	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	139	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.5	-0.7	-0.9	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} = -4.5V, I _D = -3A	-	49	64	mΩ
		V _{GS} = -2.5V, I _D = -2A	-	59	89	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz	-	550	-	pF
C _{oss}	Output Capacitance		-	89	-	pF
C _{rss}	Reverse Transfer Capacitance		-	65	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -3A, V _{GS} = -4.5V	-	4.3	-	nC
Q _{gs}	Gate-Source Charge		-	0.8	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	1.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, I _D = -3A, R _G = 1Ω, V _{GEN} = -4.5V, R _L =1.2Ω	-	12	-	ns
t _r	Turn-on Rise Time		-	54	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-3	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-12	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -3A	-	-	-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Figure1: Output Characteristics

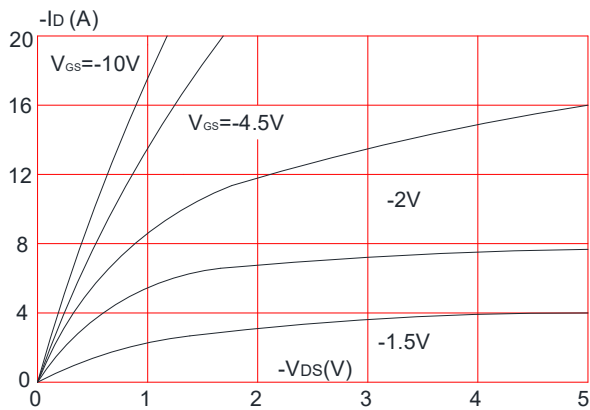


Figure 2: Typical Transfer Characteristics

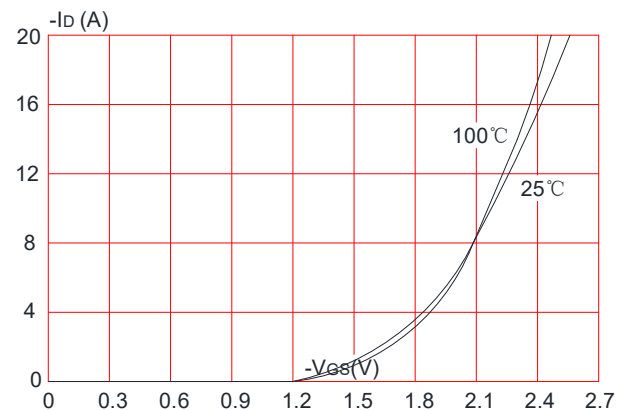


Figure 3: On-resistance vs. Drain Current

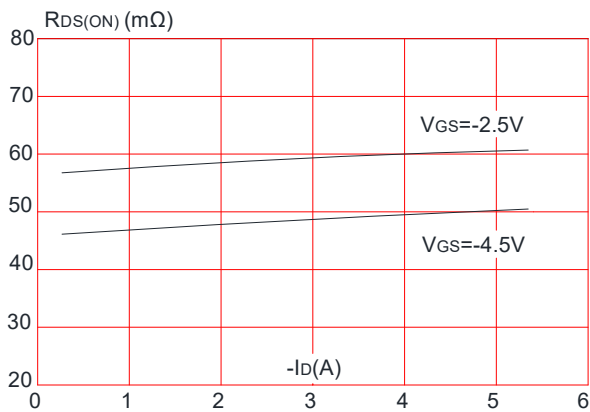


Figure 4: Body Diode Characteristics

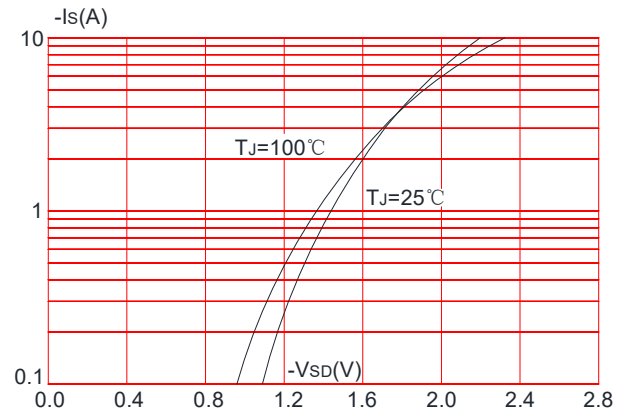


Figure 5: Gate Charge Characteristics

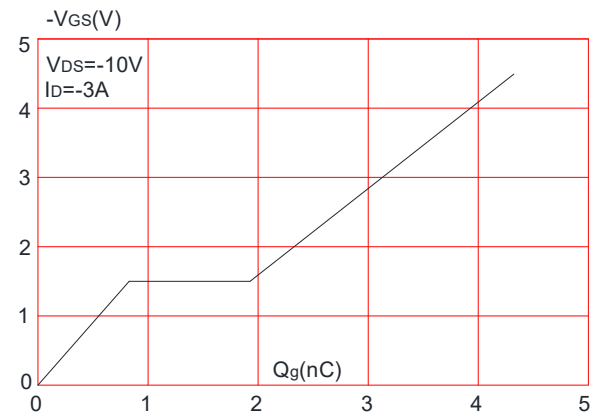


Figure 6: Capacitance Characteristics

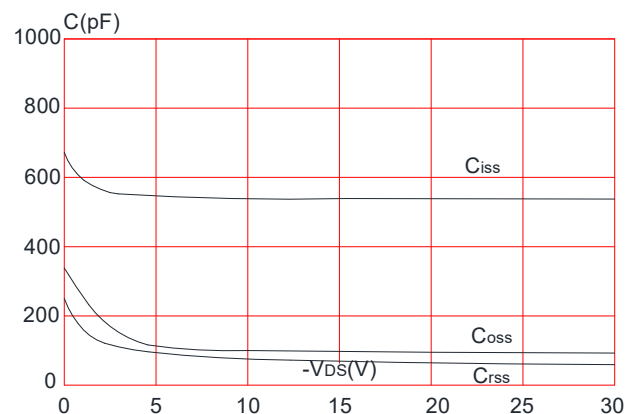


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

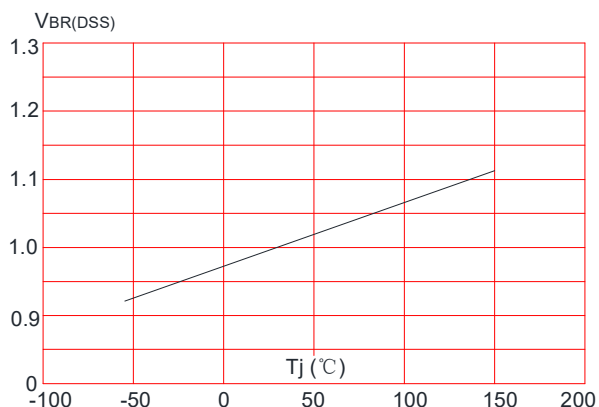


Figure 8: Normalized on Resistance vs. Junction Temperature

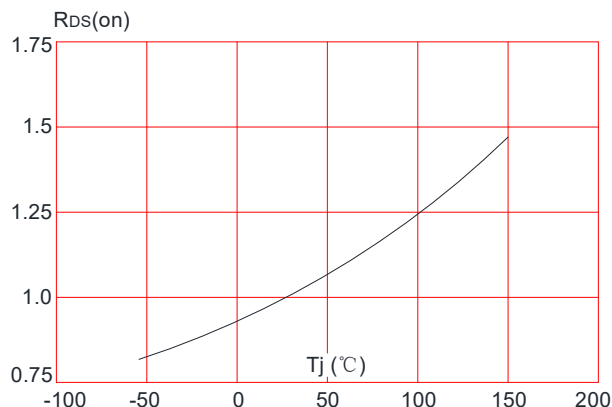


Figure 9: Maximum Safe Operating Area

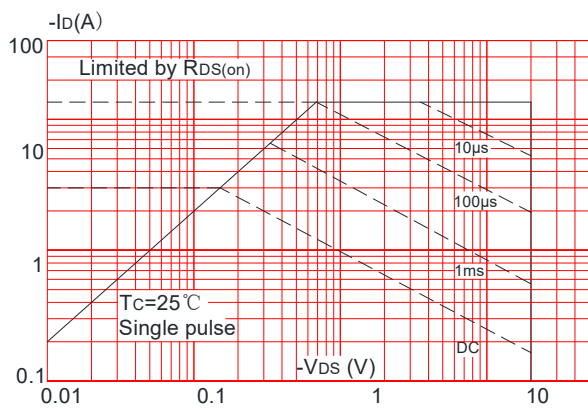


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

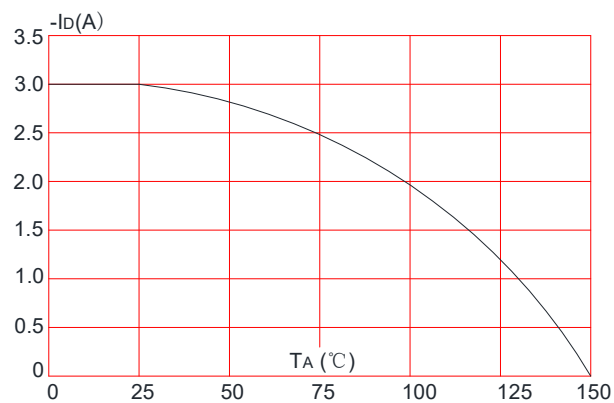
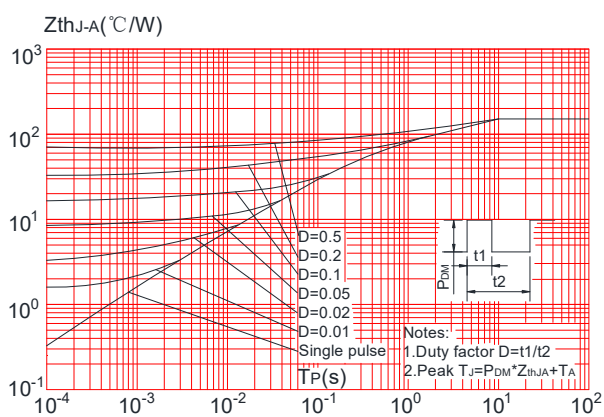
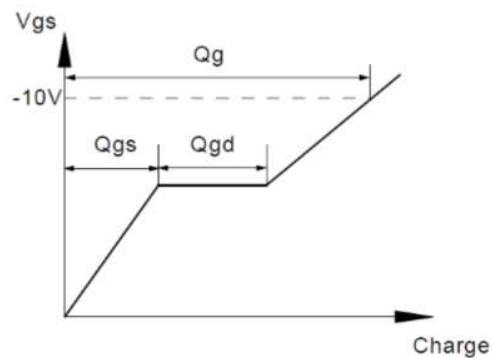
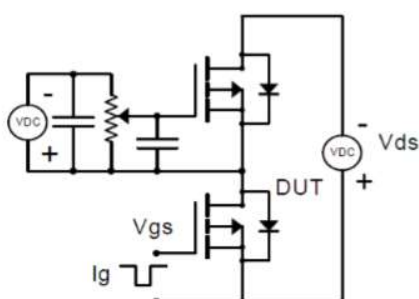


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

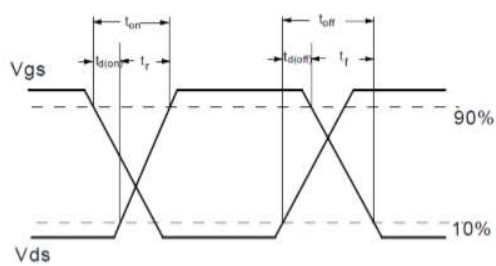
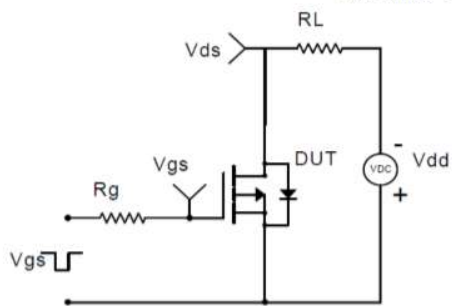


Test Circuit

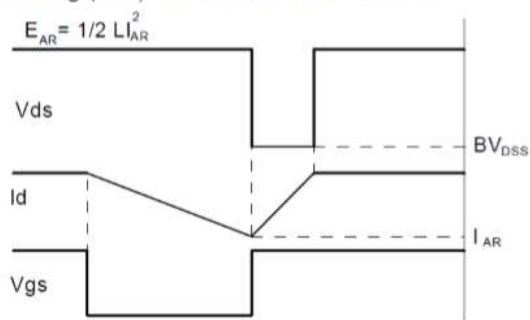
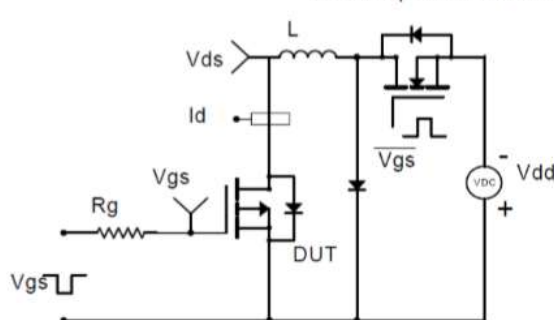
Gate Charge Test Circuit & Waveform



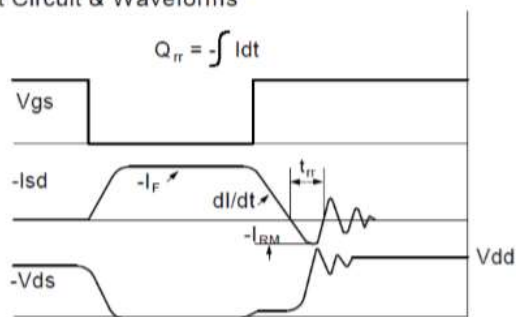
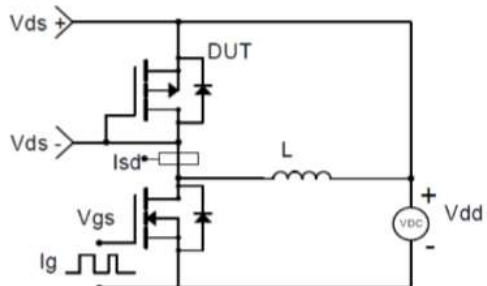
Resistive Switching Test Circuit & Waveforms



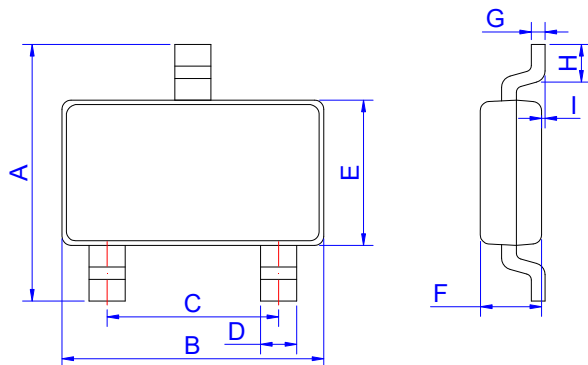
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



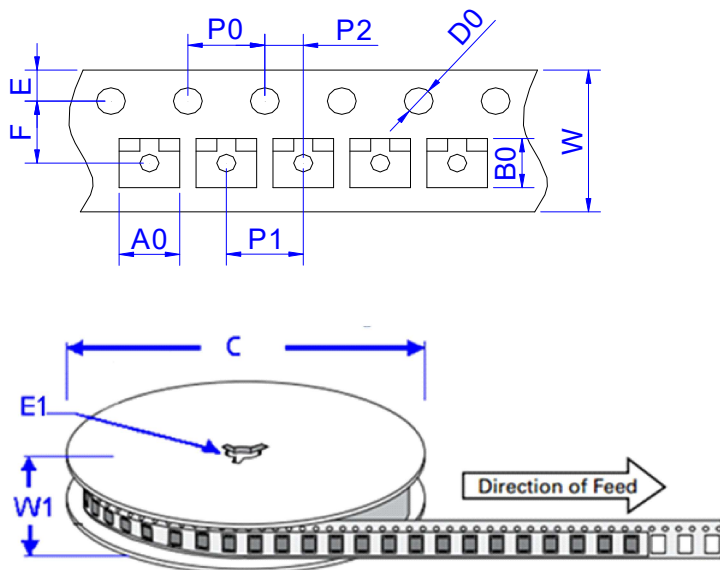
Package Mechanical Data-SOT-23



SOT-23

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039



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